

Electronic states of a new antiferromagnetic superconductor CePt₃Si

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An antiferromagnet CePt₃Si with $T_N=2.3$ K was reported to become superconductive below 0.7 K at ambient pressure[1]. Surprisingly this compound is tetragonal, space group $P4mm$ (No.99), without inversion symmetry in the crystal structure. We confirmed superconductivity in CePt₃Si and studied the fundamental properties.

Figure 1 shows the temperature dependence of the electrical resistivity in CePt₃Si and a non- $4f$ reference compound LaPt₃Si. A faint resistivity peak is observed around 75 K in CePt₃Si. This might be based on a combined phenomenon of the crystalline electric field (CEF) and Kondo effects. If this temperature corresponds to T_K^h in ref. [2], the Kondo temperature T_K is estimated as $T_K = 130$ K from a relation of $T_K^{h3} = \Delta_1 \Delta_2 T_K$, where $\Delta_1 = 12$ K and $\Delta_2 = 280$ K, obtained by the neutron scattering experiment[3], are splitting energies from the ground state of the $4f$ levels to the first and second excited levels, respectively. The relation is not applied to the resistivity in CePt₃Si.

We confirmed the Néel temperature 2.3 K, together with superconductivity below 0.7 K. We note that LaPt₃Si also becomes superconductive below 0.6 K.

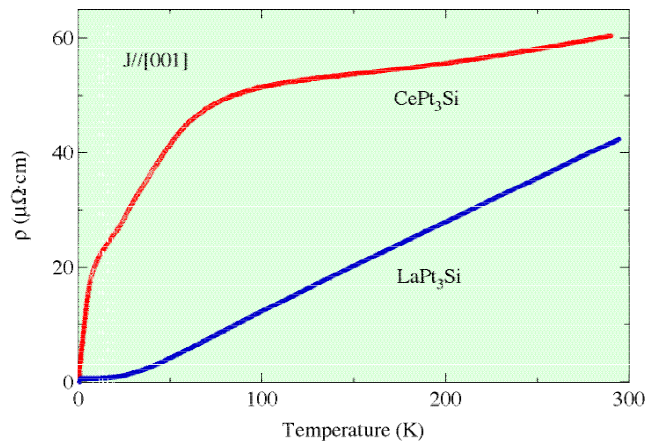


Figure 1: Temperature dependence of the electrical resistivity in CePt₃Si.

[1] E. Bauer *et al.*, Cond-mat/0308083.

[2] K. Yamada *et al.*, Prog. Theor. Phys. 71 (1984) 450.

[3] N. Metoki *et al.*, to be published.